

2SC4655J

Silicon NPN epitaxial planar type

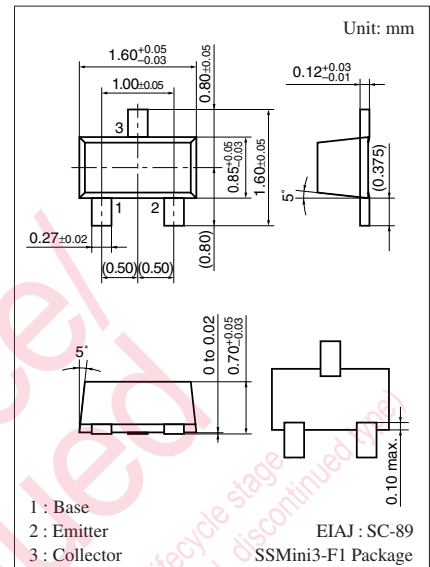
For high-frequency amplification

■ Features

- Optimum for RF amplification, oscillation, mixing, and IF of FM/SAM radios
- SS-Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

| Parameter | Symbol | Rating | Unit |
|---------------------------------------|------------------|-------------|------------------|
| Collector-base voltage (Emitter open) | V_{CBO} | 30 | V |
| Collector-emitter voltage (Base open) | V_{CEO} | 20 | V |
| Emitter-base voltage (Collector open) | V_{EBO} | 5 | V |
| Collector current | I_{C} | 30 | mA |
| Collector power dissipation | P_{C} | 125 | mW |
| Junction temperature | T_{j} | 125 | $^\circ\text{C}$ |
| Storage temperature | T_{stg} | -55 to +125 | $^\circ\text{C}$ |



Marking Symbol: K

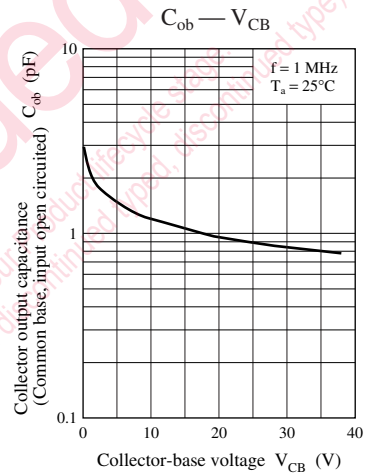
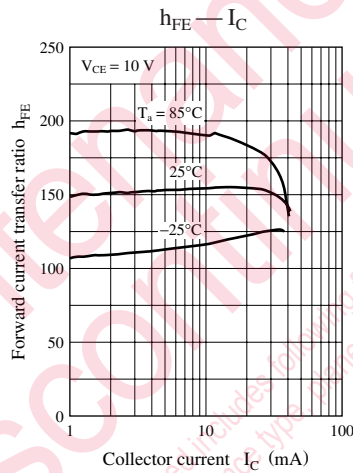
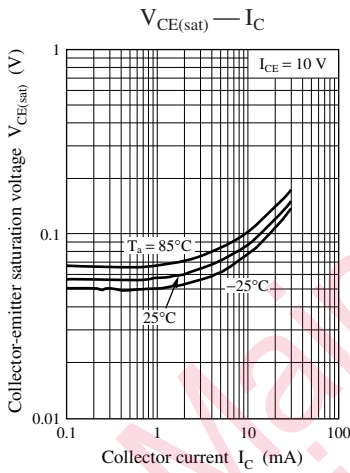
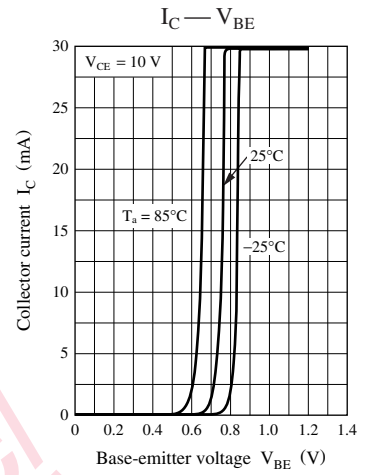
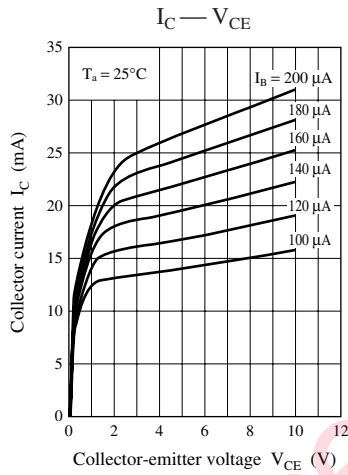
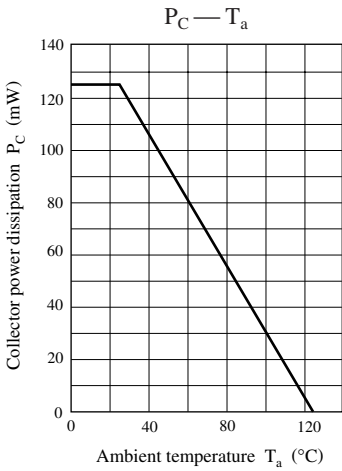
■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

| Parameter | Symbol | Conditions | Min | Typ | Max | Unit |
|---|------------------|--|-----|-----|-----|------|
| Collector-base voltage (Emitter open) | V_{CBO} | $I_{\text{C}} = 10 \mu\text{A}, I_{\text{E}} = 0$ | 30 | | | V |
| Collector-emitter voltage (Base open) | V_{CEO} | $I_{\text{C}} = 2 \text{ mA}, I_{\text{B}} = 0$ | 20 | | | V |
| Emitter-base voltage (Collector open) | V_{EBO} | $I_{\text{E}} = 10 \mu\text{A}, I_{\text{C}} = 0$ | 5 | | | V |
| Forward current transfer ratio * | h_{FE} | $V_{\text{CE}} = 10 \text{ V}, I_{\text{C}} = 1 \text{ mA}$ | 70 | | 250 | — |
| Transition frequency | f_{T} | $V_{\text{CB}} = 10 \text{ V}, I_{\text{E}} = -1 \text{ mA}, f = 200 \text{ MHz}$ | 150 | 230 | | MHz |
| Reverse transfer capacitance (Common emitter) | C_{re} | $V_{\text{CB}} = 10 \text{ V}, I_{\text{E}} = -1 \text{ mA}, f = 10.7 \text{ MHz}$ | | 1.3 | | pF |

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *: Rank classification

| Rank | B | C |
|-----------------|-----------|------------|
| h_{FE} | 70 to 160 | 110 to 250 |



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